

# **TN6718A**



# **NPN General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0A. Sourced from Process 39. See TN6717A for characteristics.

### Absolute Maximum Ratings\*

T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V
V <sub>CBO</sub>	Collector-Base Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	1.2	Α
T <sub>J, Tstg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 °C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics \_\_\_\_ T\_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN6718A	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	1 8	W mW/°C
R <sub>0</sub> JC	Thermal Resistance, Junction to Case	50	°C/W
R <sub>θ</sub> JA	Thermal Resistance, Junction to Ambient	125	°C/W

## NPN General Purpose Amplifier

(continued)

### **Electrical Characteristics**

T<sub>A = 25°C</sub> unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	100		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA	100		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA	5		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> =80 V		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5 V		10	uA
ON CHAF	RACTERISTICS				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 1 V	80		-
		$I_C = 250 \text{ mA}, V_{CE} = 1 \text{ V}$	50	250	
		$I_C = 500 \text{ mA}, V_{CE} = 1 \text{ V}$	20		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 250 mA, I <sub>B</sub> = 10 mA		0.5	V
		$I_C = 250 \text{ mA}, I_B = 25 \text{ mA}$		0.35	
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 250 mA, V <sub>CE</sub> = 1 V		1.2	V
SMALL S	GNAL CHARACTERISTICS				
C <sub>cb</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz		30	pF
h <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 200 mA, V <sub>CE</sub> = 5 V, f=20MHz	2.5	25	-

\*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 1.0%

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